Register No:	Name:

SAINTGITS COLLEGE OF ENGINEERING (AUTONOMOUS)

(AFFILIATED TO APJ ABDUL KALAM TECHNOLOGICAL UNIVERSITY, THIRUVANANTHAPURAM)

FIRST SEMESTER B.TECH DEGREE EXAMINATION(R), NOVEMBER 2024

Common to Electronics and Communication Engineering & Electonics Engineering (VLSI Design and Technlogy)

(2024 SCHEME)

Course Code : 24EST1004-J

Course Name : Semiconductor Physics and Devices

Max. Marks : 60 Duration: 2.5 Hours

PART A

(Answer all questions. Each question carries 3 marks)

- 1. Why is Fermi level important in determining the electrical properties of a material?
- 2. What is the significance of the saturation current (Io) in the diode current equation?
- 3. Why is transistor considered a current-controlled device?
- 4. Write the equation for transconductance gm in a MOSFET and explain terms.
- 5. Which parameter determines the colour of light emitted by an LED?

PART B

(Answer one full question from each module, each question carries 9 marks)

MODULE I

6. Explain what happens to s and p subshells of outermost shell, when neighbouring atoms interact in 9 the crystal structure of Silicon.

OR

7. Explain Fermi Dirac distribution. Compare the behavior of Fermi-Dirac distribution function at different temperatures.

MODULE II

8. Discuss the role of the depletion region in preventing current flow under equilibrium conditions in 9 a PN junction. How does the width of the depletion region vary with doping levels?

OF

9. Explain the two main mechanisms of reverse breakdown in a PN junction diode.

MODULE III

10. Discuss the current gain gama (γ) in the Common Collector (CC) configuration. Derive the 9 relationship between β and γ .

OR

11. Explain the input and output characteristics of Common Emitter configuration.

MODULE IV

12. Explain the VI characteristics of JFET.

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OR

13. Explain the VI characteristics of MOSFET.

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MODULE V

14.	Describe the structure and working of Photo Diode.	9
	OR	
15.	Describe the structure and operation of Varactor Diode.	9
